/ Descriptions

TO-92 PNP Silicon PNP transistor in a TO-92 Plastic Package.

/ Features

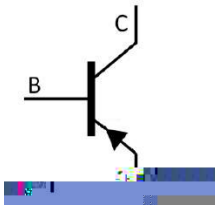
h_{FE},

Low noise, high h_{FE}, high breakdown voltage.

/ Applications

Low noise audio amplifier application.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ hFE Classifications & Marking

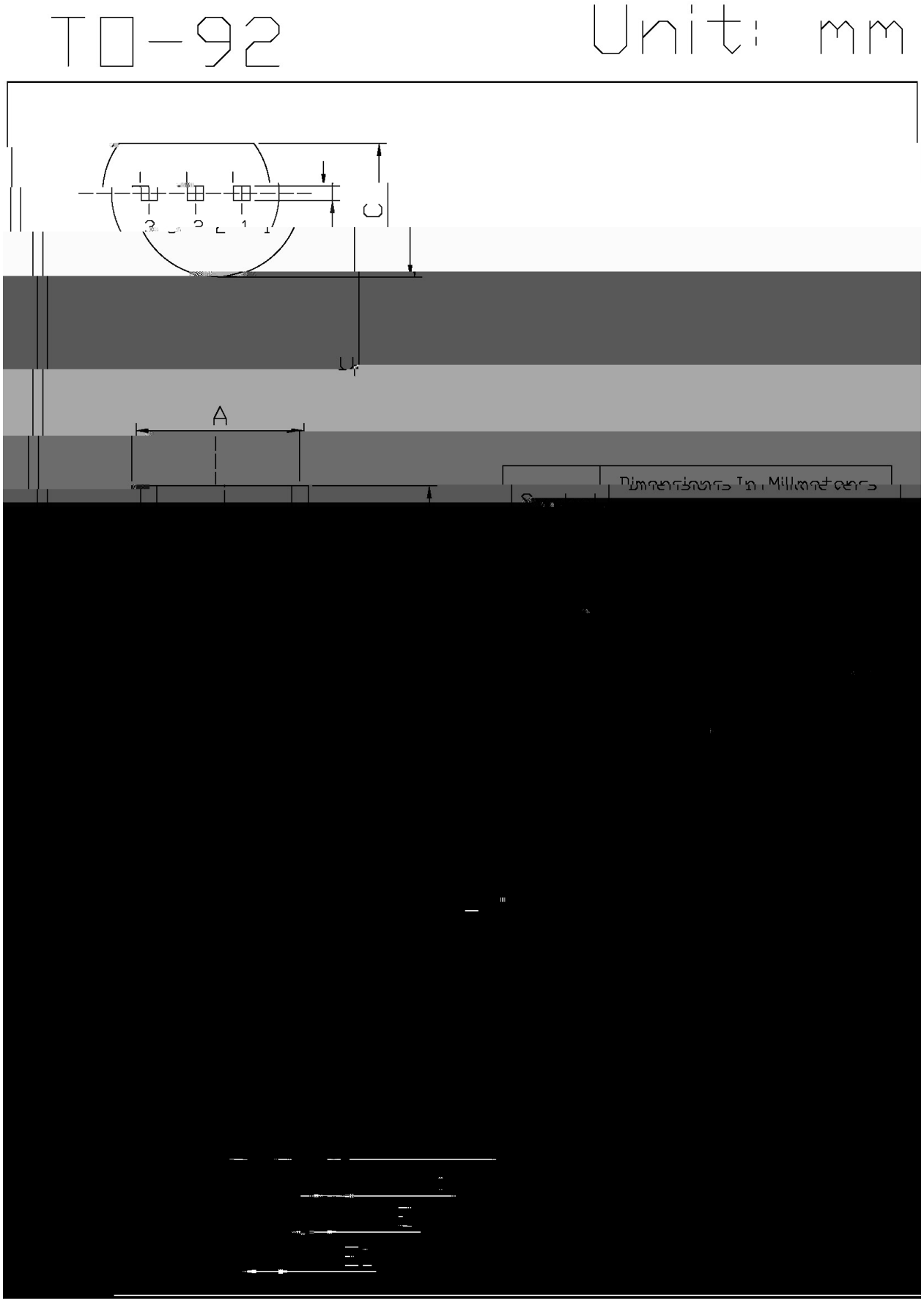
h_{FE} Classifications Symbol	Y	GR	BL
h_{FE} Range	120~240	200~400	350~700

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-120	V
Collector to Emitter Voltage	V_{CEO}	-120	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

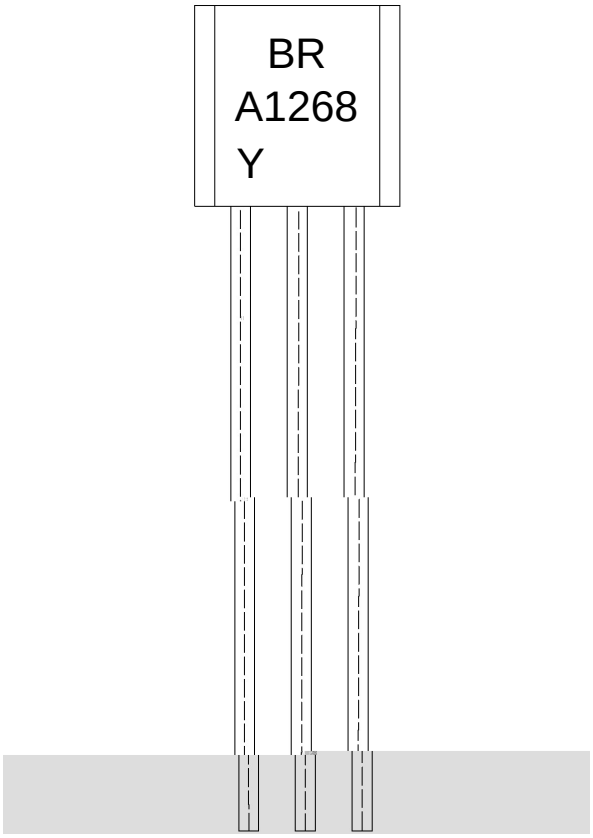
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-120			V
Collector to Base Breakdown Voltage	V_{CBO}	I_C=100μA I_E=0	-120			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=100μA I_C=0	-5.0			V

Collector Cut-Off Current V I

/ Package Dimensions



/ Marking Instructions



BR:

A1268

Y: h_{FE}

****

Note:

BR:	Company Code.
A1268:	Product Type.
Y:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



					Note:
1	25	150	60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5			5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension		(unit mm3)

/ AMMO

Package Type	Units					Dimension	(unit mm3)

/ Notices